

isc N-Channel MOSFET Transistor

2SK3688-01L

FEATURES

- Drain Current : I_D= 16A@ T_C=25 $^\circ\!\mathrm{C}$
- Drain Source Voltage : V_{DSS}= 600V(Min)
- Static Drain-Source On-Resistance
- : R_{DS(on)} = 0.57 Ω (Max) @ V_{GS}= 10V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

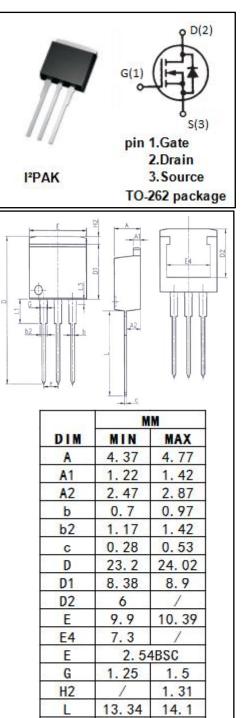
DESCRIPTION

 motor drive, DC-DC converter, power switch and solenoid drive.

| ABSOLUTE MAXIMUM RATINGS(Ta=25°C) | | | | | | | |
|-------------------------------------|--|---|--|--|--|--|--|
| PARAMETER | VALUE | UNIT | | | | | |
| Drain-Source Voltage | 600 | V | | | | | |
| Gate-Source Voltage-Continuous | ±30 | V | | | | | |
| Drain Current-Continuous | 16 | А | | | | | |
| Drain Current-Single Pluse | 64 | А | | | | | |
| Total Dissipation @Tc=25℃ | 270 | W | | | | | |
| Max. Operating Junction Temperature | -55~150 | °C | | | | | |
| Storage Temperature | -55~150 | °C | | | | | |
| | Drain-Source Voltage Gate-Source Voltage-Continuous Drain Current-Continuous Drain Current-Single Pluse Total Dissipation @Tc=25°C Max. Operating Junction Temperature | Drain-Source Voltage600Gate-Source Voltage-Continuous±30Drain Current-Continuous16Drain Current-Single Pluse64Total Dissipation @Tc=25°C270Max. Operating Junction Temperature-55~150 | | | | | |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT | |
|---------------------|--------------------------------------|-------|------|--|
| R _{th j-c} | Thermal Resistance, Junction to Case | 0.463 | °C/W | |



isc website: <u>www.iscsemi.com</u>

L1 L3 3.3

0.95

4.06

1.15



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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | МАХ | UNIT |
|----------------------|---------------------------------|--|-----|------|------|
| V _{(BR)DSS} | Drain-Source Breakdown Voltage | V _{GS} = 0; I _D = 0.25mA | 600 | | V |
| V _{GS} (th) | Gate Threshold Voltage | V _{DS} = 10V; I _D = 0.25mA | 3.0 | 5.0 | V |
| R _{DS} (on) | Drain-Source On-Resistance | V _{GS} = 10V; I _D = 8.0A | | 0.57 | Ω |
| I _{GSS} | Gate-Body Leakage Current | V _{GS} = ±30V;V _{DS} = 0 | | ±0.1 | uA |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = 600V; V _{GS} = 0 | | 25 | uA |
| V _{SD} | Forward On-Voltage | I _S = 16A; V _{GS} = 0 | | 1.5 | V |

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